High Reliability 2.28-inch Dual-Color 5mm 8×8 Dot Matrix LED Displays

SDM-5882
SDM-5889

단종품

GENERAL DESCRIPTION

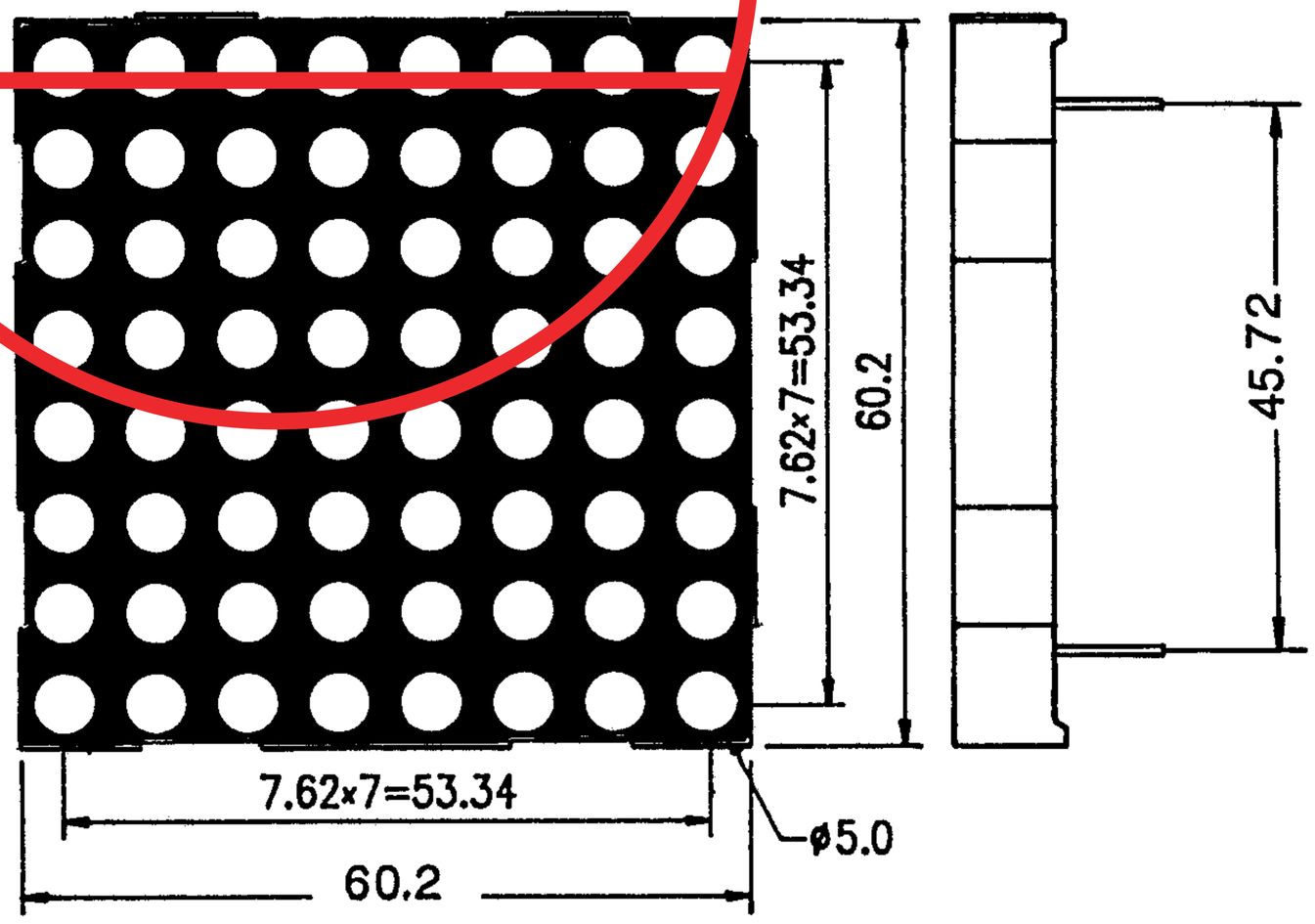
The SDM-5882 and the SDM-5889 series are an epoxy molded 2.28 in. (58.0mm) height, 5mm diameter and 8×8 dot matrix dual color LED displays. A red and green chips are contained in each dots and it could be displayed in red or green color separately and also appears in amber color when drive to red and green in the same time.

FEATURES

1. High brightness with high contrast
2. Wide angle viewing
3. Low power consumption;
   Directly drive with I.C
4. Solid state reliability;
   Long operation life
5. Cathode- row (SDM5882) and cathode column (SDM-5889) types available

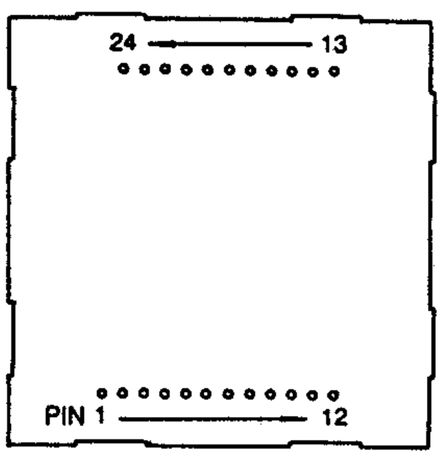
PACKAGE DIMENSIONS

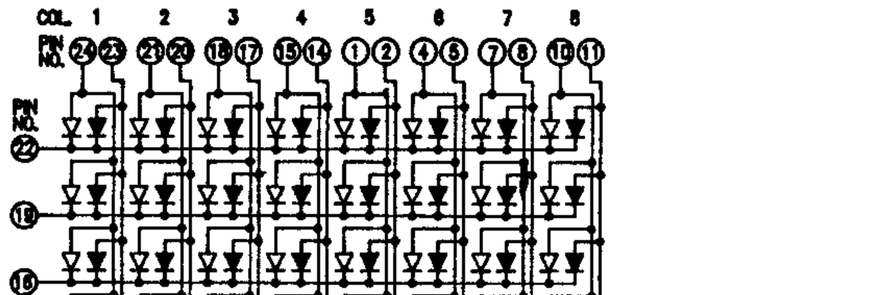
SCALE 1:1 (mm)



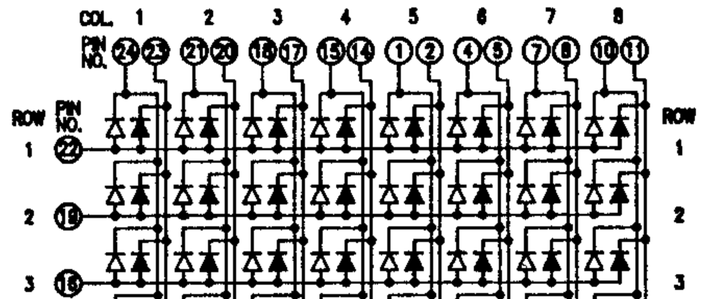
CONNECTIONS GUIDE

(Top View)





SDM 5882 (Cathode Row)



SDM 5889 (Cathode Column)

三光半導体株式會社
SAM KWANG SEMICONDUCTOR CO.,LTD.
803 Silla Techno Vil., 39-3 Dang-dong Kunpo-City Kyungki-do, Korea,
TEL:031-456-1444/1484, FAX:031-456-4224

SDM 5882/5889 SR-UG (GaAsP/GaP-GaP)

Orange SR SIDE (GaAsP/GaP)

Absolute Maximum Ratings (T_a=25°C)

Power dissipation/Total	4000	mW
Power dissipation/Chip	30	mW
Forward current	15	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	−25 ~ +85	°C
Storage temperature	−55 ~ +100	°C

Electrical/Optical Characteristics (T_a=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	I_F = 10mA	—	2.0	2.2	V
Reverse current/Chip	I_R	V_R = 4V	—	—	10	μA
Luminous Intensity/Chip	I_V	I_F = 10mA	500	1000	—	μcd
Peak wavelength	λ_P	I_F = 10mA	—	635	—	nm
Spectral line halfwidth	$\Delta\lambda$	I_F = 10mA	—	35	—	nm

Yellow-green UG SIDE (GaP)

Absolute Maximum Ratings (T_a=25°C)

Power dissipation/Total	4000	mW
Power dissipation/Chip	30	mW
Forward current	15	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	−25 ~ +85	°C
Storage temperature	−55 ~ +100	°C

Electrical/Optical Characteristics (T_a=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	I_F = 10mA	—	2.1	2.3	V
Reverse current/Chip	I_R	V_R = 4V	—	—	10	μA
Luminous Intensity/Chip	I_V	I_F = 10mA	600	1200	—	μcd
Peak wavelength	λ_P	I_F = 10mA	—	565	—	nm
Spectral line halfwidth	$\Delta\lambda$	I_F = 10mA	—	30	—	nm

* Pulse Width ..... 1 ms
Duty Cycle 1/5